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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	684
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	104
Number of Gates	4000
Voltage - Supply	4.5V ~ 5.5V
Mounting Type	Through Hole
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	132-BCPGA
Supplier Device Package	132-CPGA (34.54x34.54)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a1240a-pg132c

Microsemi®

1 – ACT 2 Family Overview

General Description

The ACT 2 family represents Actel's second generation of field programmable gate arrays (FPGAs). The ACT 2 family presents a two-module architecture, consisting of C-modules and S-modules. These modules are optimized for both combinatorial and sequential designs. Based on Actel's patented channeled array architecture, the ACT 2 family provides significant enhancements to gate density and performance while maintaining downward compatibility with the ACT 1 design environment and upward compatibility with the ACT 3 design environment. The devices are implemented in silicon gate, 1.0-µm, two-level metal CMOS, and employ Actel's PLICE® antifuse technology. This revolutionary architecture offers gate array design flexibility, high performance, and fast time-to-production with user programming. The ACT 2 family is supported by the Designer and Designer Advantage Systems, which offers automatic pin assignment, validation of electrical and design rules, automatic placement and routing, timing analysis, user programming, and diagnostic probe capabilities. The systems are supported on the following platforms: 386/486™ PC, Sun™, and HP™ workstations. The systems provide CAE interfaces to the following design environments: Cadence, Viewlogic®, Mentor Graphics®, and OrCAD™.

2 – Detailed Specifications

Operating Conditions

Table 2-1 • **Absolute Maximum Ratings[1]**

Symbol	Parameter	Limits	Units
VCC	DC supply voltage	–0.5 to +7.0	V
VI	Input voltage	–0.5 to VCC + 0.5	V
VO	Output voltage	–0.5 to VCC + 0.5	V
IIO	I/O source sink current[2]	±20	mA
T_{STG}	Storage temperature	–65 to +150	°C

Notes:

1. *Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Device should not be operated outside the recommended operating conditions.*
2. *Device inputs are normally high impedance and draw extremely low current. However, when input voltage is greater than VCC + 0.5 V for less than GND –0.5 V, the internal protection diodes will be forward biased and can draw excessive current.*

Table 2-2 • **Recommended Operating Conditions**

Parameter	Commercial	Industrial	Military	Units
Temperature range*	0 to +70	–40 to +85	–55 to +125	°C
Power supply tolerance	±5	±10	±10	%VCC

*Note: *Ambient temperature (T_A) is used for commercial and industrial; case temperature (T_C) is used for military.*

Table 2-3 • Electrical Specifications

Symbol	Parameter	Commercial		Industrial		Military		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
VOH[1]	(IOH = –10 mA)[2]	2.4	–	–	–	–	–	V
	(IOH = –6 mA)	3.84	–	–	–	–	–	V
	(IOH = –4 mA)	–	–	3.7	–	3.7	–	V
VOL[1]	(IOL = 10 mA)[2]	–	0.5	–	–	–	–	V
	(IOL = 6 mA)	–	0.33	–	0.40	–	0.40	V
VIL		–0.3	0.8	–0.3	0.8	–0.3	0.8	V
VIH		2.0	VCC + 0.3	2.0	VCC + 0.3	2.0	VCC + 0.3	V
Input Transition Time t_R, t_F[2]		–	500	–	500	–	500	ns
C_{IO} I/O capacitance[2,3]		–	10	–	10	–	10	pF
Standby Current, ICC[4] (typical = 1 mA)		–	2	–	10	–	20	mA
Leakage Current[5]		–10	+10	–10	+10	–10	+10	µA
ICC(D)	Dynamic VCC supply current. See the Power Dissipation section.							

Notes:

1. *Only one output tested at a time. VCC = minimum.*
2. *Not tested, for information only.*
3. *Includes worst-case PG176 package capacitance. VOUT = 0 V, f = 1 MHz*
4. *All outputs unloaded. All inputs = VCC or GND, typical ICC = 1 mA. ICC limit includes IPP and ISV during normal operations.*
5. *VOUT, VIN = VCC or GND.*

Static Power Component

Microsemi FPGAs have small static power components that result in lower power dissipation than PALs or PLDs. By integrating multiple PALs/PLDs into one FPGA, an even greater reduction in board-level power dissipation can be achieved.

The power due to standby current is typically a small component of the overall power. Standby power is calculated in Table 2-5 for commercial, worst case conditions.

***Table 2-5* • Standby Power Calculation**

ICC	VCC	Power
2 mA	5.25 V	10.5 mW

The static power dissipated by TTL loads depends on the number of outputs driving high or low and the DC load current. Again, this value is typically small. For instance, a 32-bit bus sinking 4 mA at 0.33 V will generate 42 mW with all outputs driving low, and 140 mW with all outputs driving high. The actual dissipation will average somewhere between as I/Os switch states with time.

Active Power Component

Power dissipation in CMOS devices is usually dominated by the active (dynamic) power dissipation. This component is frequency dependent, a function of the logic and the external I/O. Active power dissipation results from charging internal chip capacitances of the interconnect, unprogrammed antifuses, module inputs, and module outputs, plus external capacitance due to PC board traces and load device inputs.

An additional component of the active power dissipation is the totem-pole current in CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent active power dissipation.

Equivalent Capacitance

The power dissipated by a CMOS circuit can be expressed by EQ 3.

$$\text{Power } (\mu W) = C_{EQ} * VCC^2 * F \qquad \textit{EQ 3}$$

Where:

C_{EQ} is the equivalent capacitance expressed in pF.

VCC is the power supply in volts.

F is the switching frequency in MHz.

Equivalent capacitance is calculated by measuring ICC active at a specified frequency and voltage for each circuit component of interest. Measurements have been made over a range of frequencies at a fixed value of VCC. Equivalent capacitance is frequency independent so that the results may be used over a wide range of operating conditions. Equivalent capacitance values are shown in Table 2-6.

***Table 2-6* • CEQ Values for Microsemi FPGAs**

Item	CEQ Value
Modules (C_{EQM})	5.8
Input Buffers (C_{EQI})	12.9
Output Buffers (C_{EQO})	23.8
Routed Array Clock Buffer Loads (C_{EQCR})	3.9

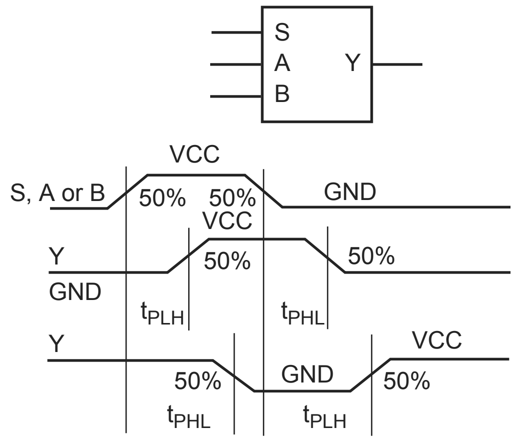
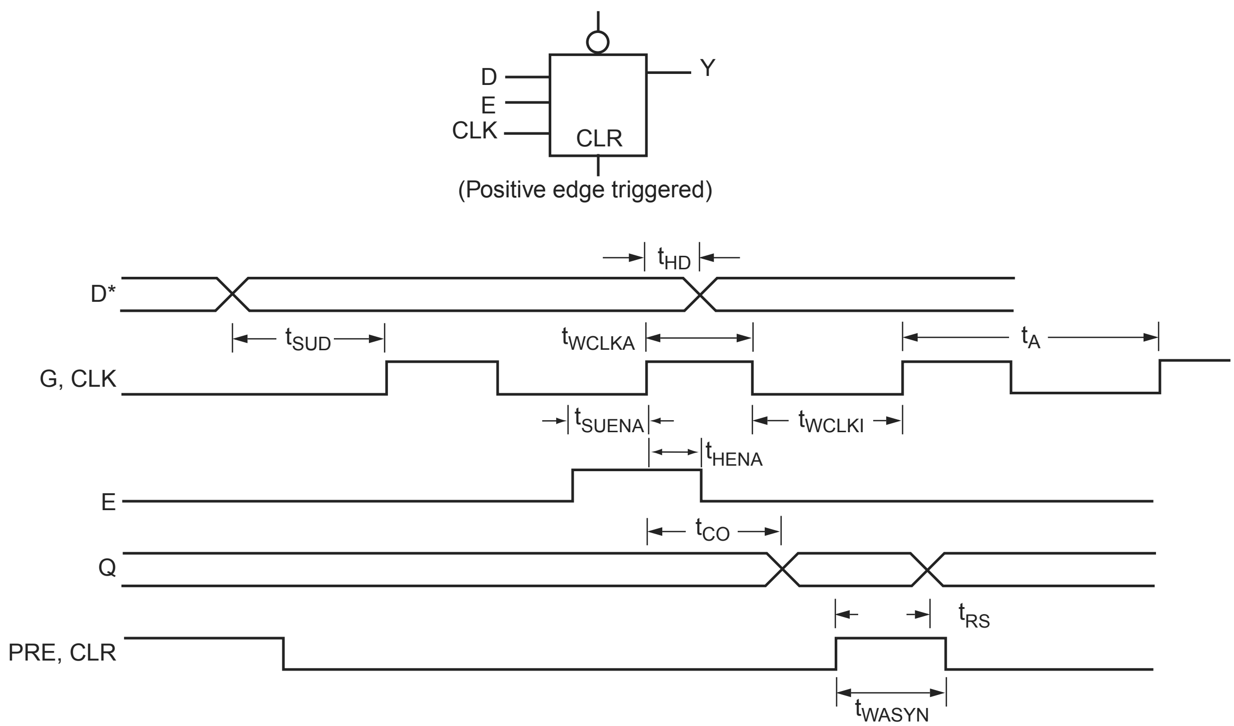


Figure 2-5 • **Module Delays**

Sequential Module Timing Characteristics



Note: D represents all data functions involving A, B, and S for multiplexed flip-flops.

Figure 2-6 • **Flip-Flops and Latches**

A1225A Timing Characteristics (continued)

Table 2-13 **• A1225A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C**

I/O Module Input Propagation Delays			–2 Speed		–1 Speed		Std. Speed		Units
Parameter/Description			**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	
t_{INYH}	Pad to Y High			2.9		3.3		3.8	ns
t_{INYL}	Pad to Y Low			2.6		3.0		3.5	ns
t_{INGH}	G to Y High			5.0		5.7		6.6	ns
t_{INGL}	G to Y Low			4.7		5.4		6.3	ns
Input Module Predicted Input Routing Delays*									
t_{IRD1}	FO = 1 Routing Delay			4.1		4.6		5.4	ns
t_{IRD2}	FO = 2 Routing Delay			4.6		5.2		6.1	ns
t_{IRD3}	FO = 3 Routing Delay			5.3		6.0		7.1	ns
t_{IRD4}	FO = 4 Routing Delay			5.7		6.4		7.6	ns
t_{IRD8}	FO = 8 Routing Delay			7.4		8.3		9.8	ns
Global Clock Network									
t_{CKH}	Input Low to High	FO = 32		10.2		11.0		12.8	ns
		FO = 256		11.8		13.0		15.7	
t_{CKL}	Input High to Low	FO = 32		10.2		11.0		12.8	ns
		FO = 256		12.0		13.2		15.9	
t_{PWH}	Minimum Pulse Width High	FO = 32	3.4		4.1		4.5		ns
		FO = 256	3.8		4.5		5.0		
t_{PWL}	Minimum Pulse Width Low	FO = 32	3.4		4.1		4.5		ns
		FO = 256	3.8		4.5		5.0		
t_{CKSW}	Maximum Skew	FO = 32		0.7		0.7		0.7	ns
		FO = 256		3.5		3.5		3.5	
t_{SUEXT}	Input Latch External Setup	FO = 32	0.0		0.0		0.0		ns
		FO = 256	0.0		0.0		0.0		
t_{HEXT}	Input Latch External Hold	FO = 32	7.0		7.0		7.0		ns
		FO = 256	11.2		11.2		11.2		
t_P	Minimum Period	FO = 32	7.7		8.3		9.1		ns
		FO = 256	8.1		8.8		10.0		
f_{MAX}	Maximum Frequency	FO = 32		130.0		120.0		110.0	ns
		FO = 256		125.0		115.0		100.0	

*Note: *These parameters should be used for estimating device performance. Optimization techniques may further reduce delays by 0 to 4 ns. Routing delays are for typical designs across worst-case operating conditions. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.*

A1225A Timing Characteristics (continued)

Table 2-14 • A1225A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C

TTL Output Module Timing[1]		–2 Speed		–1 Speed		Std. Speed		Units
Parameter/Description		Min.	Max.	Min.	Max.	Min.	Max.	
t_{DLH}	Data to Pad High		8.0		9.0		10.6	ns
t_{DHL}	Data to Pad Low		10.1		11.4		13.4	ns
t_{ENZH}	Enable Pad Z to High		8.9		10.0		11.8	ns
t_{ENZL}	Enable Pad Z to Low		11.6		13.2		15.5	ns
t_{ENHZ}	Enable Pad High to Z		7.1		8.0		9.4	ns
t_{ENLZ}	Enable Pad Low to Z		8.3		9.5		11.1	ns
t_{GLH}	G to Pad High		8.9		10.2		11.9	ns
t_{GHL}	G to Pad Low		11.2		12.7		14.9	ns
d_{TLH}	Delta Low to High		0.07		0.08		0.09	ns/pF
d_{THL}	Delta High to Low		0.12		0.13		0.16	ns/pF
CMOS Output Module Timing[1]								
t_{DLH}	Data to Pad High		10.1		11.5		13.5	ns
t_{DHL}	Data to Pad Low		8.4		9.6		11.2	ns
t_{ENZH}	Enable Pad Z to High		8.9		10.0		11.8	ns
t_{ENZL}	Enable Pad Z to Low		11.6		13.2		15.5	ns
t_{ENHZ}	Enable Pad High to Z		7.1		8.0		9.4	ns
t_{ENLZ}	Enable Pad Low to Z		8.3		9.5		11.1	ns
t_{GLH}	G to Pad High		8.9		10.2		11.9	ns
t_{GHL}	G to Pad Low		11.2		12.7		14.9	ns
d_{TLH}	Delta Low to High		0.12		0.13		0.16	ns/pF
d_{THL}	Delta High to Low		0.09		0.10		0.12	ns/pF

Notes:

1. *Delays based on 50 pF loading.*
2. *SSO information can be found at www.microsemi.com/soc/techdocs/appnotes/board_consideration.aspx.*

A1240A Timing Characteristics

***Table 2-15* • A1240A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C**

Logic Module Propagation Delays[1]		–2 Speed[3]		–1 Speed		Std. Speed		Units
Parameter/Description		**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	
t_{PD1}	Single Module		3.8		4.3		5.0	ns
t_{CO}	Sequential Clock to Q		3.8		4.3		5.0	ns
t_{GO}	Latch G to Q		3.8		4.3		5.0	ns
t_{RS}	Flip-Flop (Latch) Reset to Q		3.8		4.3		5.0	ns
Predicted Routing Delays[2]								
t_{RD1}	FO = 1 Routing Delay		1.4		1.5		1.8	ns
t_{RD2}	FO = 2 Routing Delay		1.7		2.0		2.3	ns
t_{RD3}	FO = 3 Routing Delay		2.3		2.6		3.0	ns
t_{RD4}	FO = 4 Routing Delay		3.1		3.5		4.1	ns
t_{RD8}	FO = 8 Routing Delay		4.7		5.4		6.3	ns
Sequential Timing Characteristics[3,4]								
t_{SUD}	Flip-Flop (Latch) Data Input Setup	0.4		0.4		0.5		ns
t_{HD}	Flip-Flop (Latch) Data Input Hold	0.0		0.0		0.0		ns
t_{SUENA}	Flip-Flop (Latch) Enable Setup	0.8		0.9		1.0		ns
t_{HENA}	Flip-Flop (Latch) Enable Hold	0.0		0.0		0.0		ns
t_{WCLKA}	Flip-Flop (Latch) Clock Active Pulse Width	4.5		6.0		6.5		ns
t_{WASYN}	Flip-Flop (Latch) Clock Asynchronous Pulse Width	4.5		6.0		6.5		ns
t_A	Flip-Flop Clock Input Period	9.8		12.0		15.0		ns
t_{INH}	Input Buffer Latch Hold	0.0		0.0		0.0		ns
t_{INSU}	Input Buffer Latch Setup	0.4		0.4		0.5		ns
t_{OUTH}	Output Buffer Latch Hold	0.0		0.0		0.0		ns
t_{OUTSU}	Output Buffer Latch Setup	0.4		0.4		0.5		ns
f_{MAX}	Flip-Flop (Latch) Clock Frequency		100.0		80.0		66.0	MHz

Notes:

1. *For dual-module macros, use $t_{PD1} + t_{RD1} + t_{PDn}$, $t_{CO} + t_{RD1} + t_{PDn}$, or $t_{PD1} + t_{RD1} + t_{SUD}$—whichever is appropriate.*
2. *Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.*
3. *Data applies to macros based on the S-module. Timing parameters for sequential macros constructed from C-modules can be obtained from the DirectTime Analyzer utility.*
4. *Setup and hold timing parameters for the Input Buffer Latch are defined with respect to the PAD and the D input. External setup/hold timing parameters must account for delay from an external PAD signal to the G inputs. Delay from an external PAD signal to the G input subtracts (adds) to the internal setup (hold) time.*

A1280A Timing Characteristics (continued)

Table 2-19 **• A1280A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C**

I/O Module Input Propagation Delays			–2 Speed		–1 Speed		Std. Speed		Units
Parameter/Description			**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	
t_{INYH}	Pad to Y High			2.9		3.3		3.8	ns
t_{INYL}	Pad to Y Low			2.7		3.0		3.5	ns
t_{INGH}	G to Y High			5.0		5.7		6.6	ns
t_{INGL}	G to Y Low			4.8		5.4		6.3	ns
Input Module Predicted Input Routing Delays*									
t_{IRD1}	FO = 1 Routing Delay			4.6		5.1		6.0	ns
t_{IRD2}	FO = 2 Routing Delay			5.2		5.9		6.9	ns
t_{IRD3}	FO = 3 Routing Delay			5.6		6.3		7.4	ns
t_{IRD4}	FO = 4 Routing Delay			6.5		7.3		8.6	ns
t_{IRD8}	FO = 8 Routing Delay			9.4		10.5		12.4	ns
Global Clock Network									
t_{CKH}	Input Low to High	FO = 32		10.2		11.0		12.8	ns
		FO = 256		13.1		14.6		17.2	
t_{CKL}	Input High to Low	FO = 32		10.2		11.0		12.8	ns
		FO = 256		13.3		14.9		17.5	
t_{PWH}	Minimum Pulse Width High	FO = 32	5.0		5.5		6.6		ns
		FO = 256	5.8		6.4		7.6		
t_{PWL}	Minimum Pulse Width Low	FO = 32	5.0		5.5		6.6		ns
		FO = 256	5.8		6.4		7.6		
t_{CKSW}	Maximum Skew	FO = 32		0.5		0.5		0.5	ns
		FO = 256		2.5		2.5		2.5	
t_{SUEXT}	Input Latch External Setup	FO = 32	0.0		0.0		0.0		ns
		FO = 256	0.0		0.0		0.0		
t_{HEXT}	Input Latch External Hold	FO = 32	7.0		7.0		7.0		ns
		FO = 256	11.2		11.2		11.2		
t_P	Minimum Period	FO = 32	9.6		11.2		13.3		ns
		FO = 256	10.6		12.6		15.3		
f_{MAX}	Maximum Frequency	FO = 32		105.0		90.0		75.0	ns
		FO = 256		95.0		80.0		65.0	

*Note: *These parameters should be used for estimating device performance. Optimization techniques may further reduce delays by 0 to 4 ns. Routing delays are for typical designs across worst-case operating conditions. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.*

A1280A Timing Characteristics (continued)

Table 2-20 **• A1280A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C**

TTL Output Module Timing[1]		–2 Speed		–1 Speed		Std. Speed		Units
Parameter/Description		Min.	Max.	Min.	Max.	Min.	Max.	
t_{DLH}	Data to Pad High		8.1		9.0		10.6	ns
t_{DHL}	Data to Pad Low		10.2		11.4		13.4	ns
t_{ENZH}	Enable Pad Z to High		9.0		10.0		11.8	ns
t_{ENZL}	Enable Pad Z to Low		11.8		13.2		15.5	ns
t_{ENHZ}	Enable Pad High to Z		7.1		8.0		9.4	ns
t_{ENLZ}	Enable Pad Low to Z		8.4		9.5		11.1	ns
t_{GLH}	G to Pad High		9.0		10.2		11.9	ns
t_{GHL}	G to Pad Low		11.3		12.7		14.9	ns
d_{TLH}	Delta Low to High		0.07		0.08		0.09	ns/pF
d_{THL}	Delta High to Low		0.12		0.13		0.16	ns/pF
CMOS Output Module Timing[1]								
t_{DLH}	Data to Pad High		10.3		11.5		13.5	ns
t_{DHL}	Data to Pad Low		8.5		9.6		11.2	ns
t_{ENZH}	Enable Pad Z to High		9.0		10.0		11.8	ns
t_{ENZL}	Enable Pad Z to Low		11.8		13.2		15.5	ns
t_{ENHZ}	Enable Pad High to Z		7.1		8.0		9.4	ns
t_{ENLZ}	Enable Pad Low to Z		8.4		9.5		11.1	ns
t_{GLH}	G to Pad High		9.0		10.2		11.9	ns
t_{GHL}	G to Pad Low		11.3		12.7		14.9	ns
d_{TLH}	Delta Low to High		0.12		0.13		0.16	ns/pF
d_{THL}	Delta High to Low		0.09		0.10		0.12	ns/pF

Notes:

1. *Delays based on 50 pF loading.*
2. *SSO information can be found at www.microsemi.com/soc/techdocs/appnotes/board_consideration.aspx.*

PL84			
Pin Number	**A1225A Function**	**A1240A Function**	**A1280A Function**
2	CLKB, I/O	CLKB, I/O	CLKB, I/O
4	PRB, I/O	PRB, I/O	PRB, I/O
6	GND	GND	GND
10	DCLK, I/O	DCLK, I/O	DCLK, I/O
12	MODE	MODE	MODE
22	VCC	VCC	VCC
23	VCC	VCC	VCC
28	GND	GND	GND
43	VCC	VCC	VCC
49	GND	GND	GND
52	SDO	SDO	SDO
63	GND	GND	GND
64	VCC	VCC	VCC
65	VCC	VCC	VCC
70	GND	GND	GND
76	SDI, I/O	SDI, I/O	SDI, I/O
81	PRA, I/O	PRA, I/O	PRA, I/O
83	CLKA, I/O	CLKA, I/O	CLKA, I/O
84	VCC	VCC	VCC

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

PQ100	
Pin Number	**A1225A Function**
2	DCLK, I/O
4	MODE
9	GND
16	VCC
17	VCC
22	GND
34	GND
40	VCC
46	GND
52	SDO
57	GND
64	GND

PQ100	
Pin Number	**A1225A Function**
65	VCC
66	VCC
67	VCC
72	GND
79	SDI, I/O
84	GND
87	PRA, I/O
89	CLKA, I/O
90	VCC
92	CLKB, I/O
94	PRB, I/O
96	GND

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

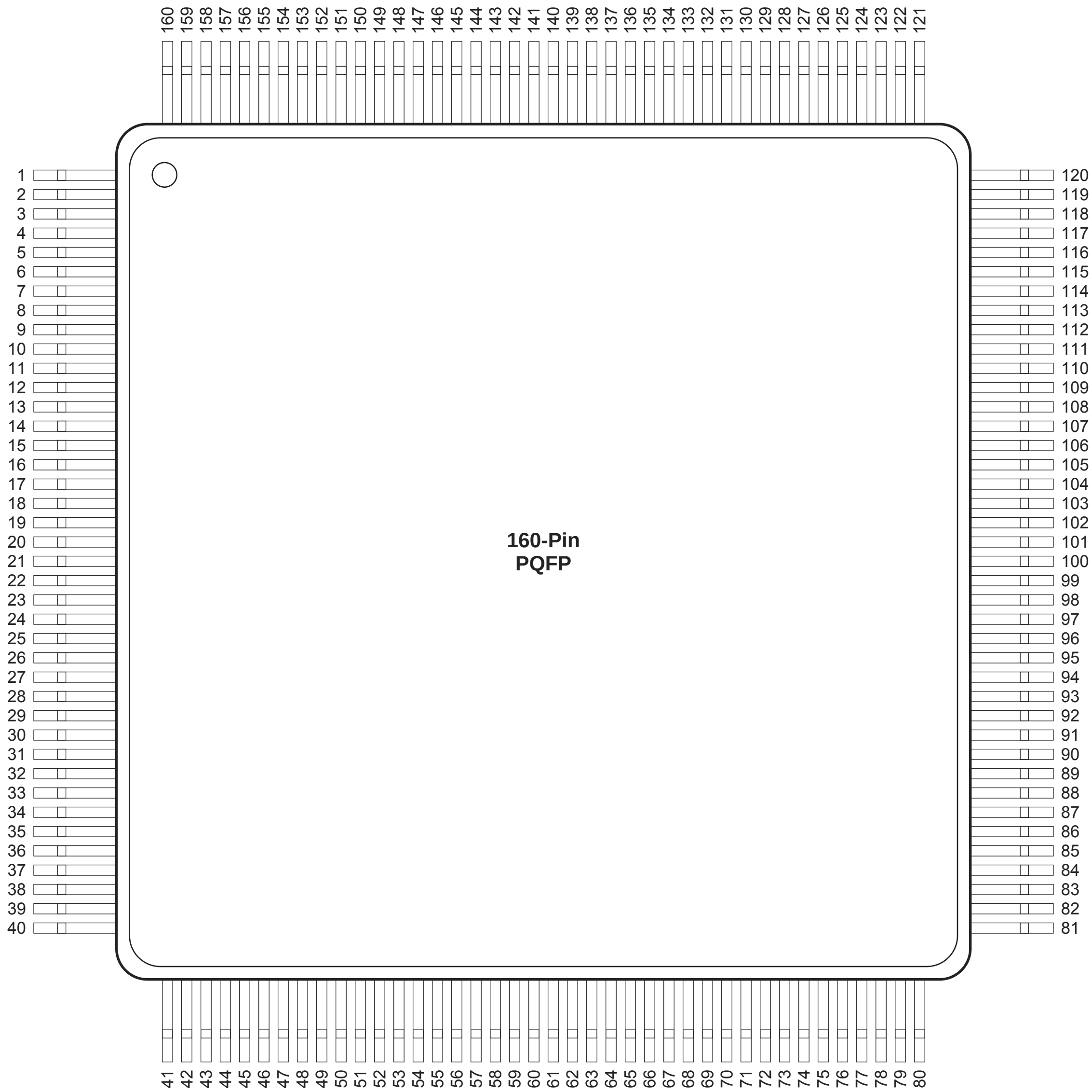
PQ144	
Pin Number	**A1240A Function**
2	MODE
9	GND
10	GND
11	GND
18	VCC
19	VCC
20	VCC
21	VCC
28	GND
29	GND
30	GND
44	GND
45	GND
46	GND
54	VCC
55	VCC
56	VCC
64	GND
65	GND
71	SDO
79	GND
80	GND
81	GND
88	GND

PQ144	
Pin Number	**A1240A Function**
89	VCC
90	VCC
91	VCC
92	VCC
93	VCC
100	GND
101	GND
102	GND
110	SDI, I/O
116	GND
117	GND
118	GND
123	PRA, I/O
125	CLKA, I/O
126	VCC
127	VCC
128	VCC
130	CLKB, I/O
132	PRB, I/O
136	GND
137	GND
138	GND
144	DCLK, I/O

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

PQ160

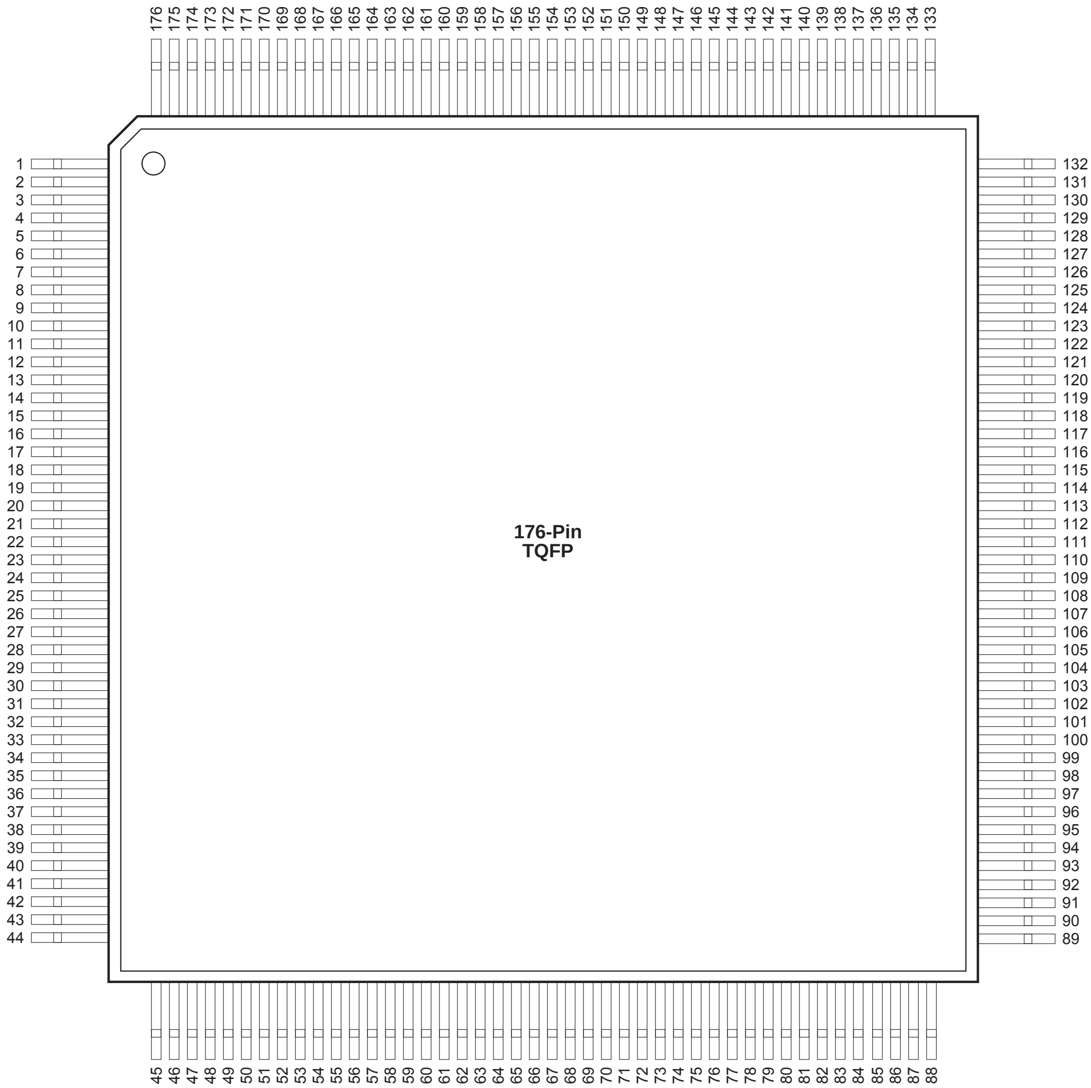


Note: This is the top view of the package

Note

For Package Manufacturing and Environmental information, visit the Resource Center at
http://www.microsemi.com/soc/products/solutions/package/docs.aspx

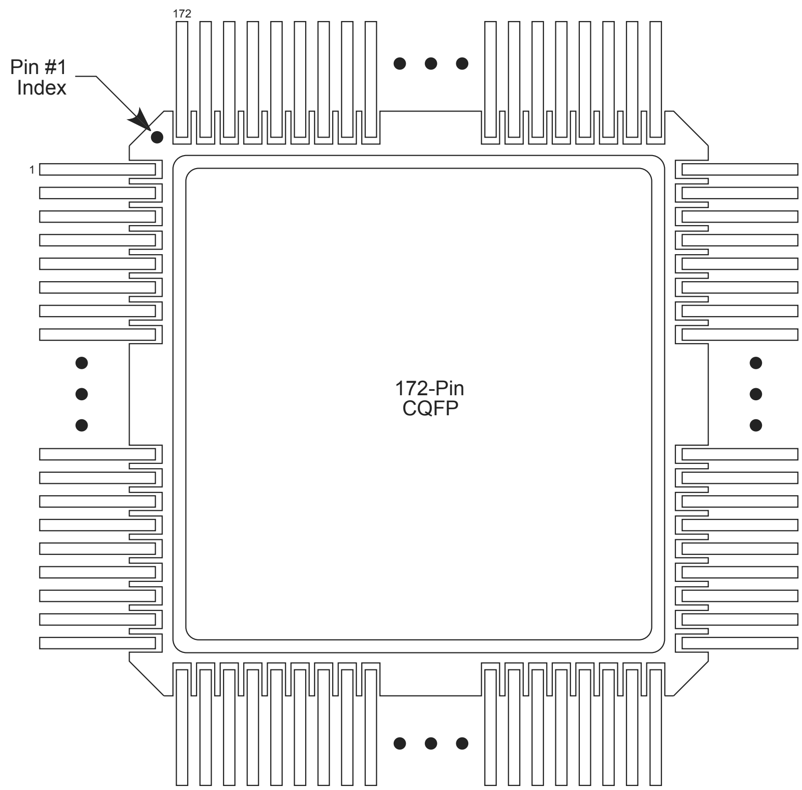
TQ176



Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx

CQ172



Note

For Package Manufacturing and Environmental information, visit the Resource Center at
http://www.microsemi.com/soc/products/solutions/package/docs.aspx

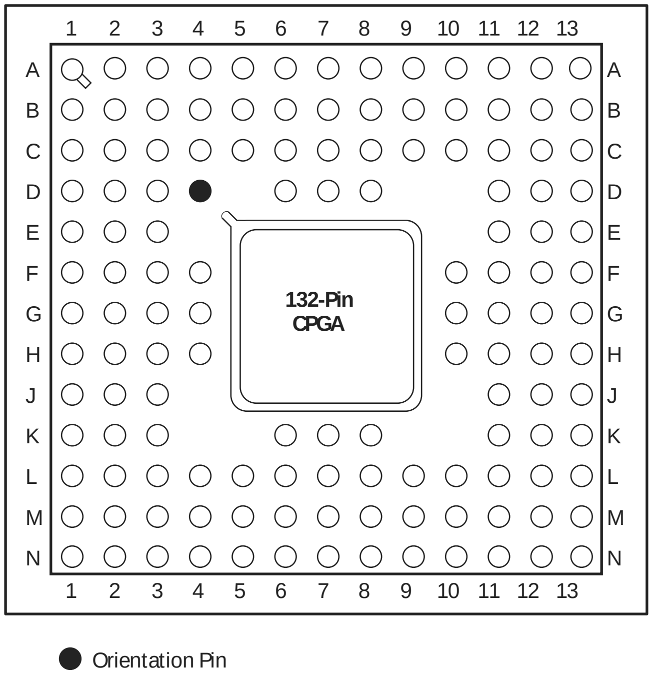
PG100	
Pin Number	**A1225A Function**
A4	PRB, I/O
A7	PRA, I/O
B6	VCC
C2	MODE
C3	DCLK, I/O
C5	GND
C6	CLKA, I/O
C7	GND
C8	SDI, I/O
D6	CLKB, I/O
D10	GND
E3	GND

PG100	
Pin Number	**A1225A Function**
E11	VCC
F3	VCC
F9	VCC
F10	VCC
F11	GND
G1	VCC
G3	GND
G9	GND
J5	GND
J7	GND
J9	SDO
K6	VCC

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

PG132



Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx

PG132	
Pin Number	**A1240A Function**
A1	MODE
B5	GND
B6	CLKB, I/O
B7	CLKA, I/O
B8	PRA, I/O
B9	GND
B12	SDI, I/O
C3	DCLK, I/O
C5	GND
C6	PRB, I/O
C7	VCC
C9	GND
D7	VCC
E3	GND
E11	GND
E12	GND
F4	GND
G2	VCC

PG132	
Pin Number	**A1240A Function**
G3	VCC
G4	VCC
G10	VCC
G11	VCC
G12	VCC
G13	VCC
H13	GND
J2	GND
J3	GND
J11	GND
K7	VCC
K12	GND
L5	GND
L7	VCC
L9	GND
M9	GND
N12	SDO

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.